# 1 Measurements & Parameter Extraction

- 1.1 Line Width/Misalignment
- 1.2 Four-Point Resistors [2a, 2b]
- 1.2.1 Measurement Setup

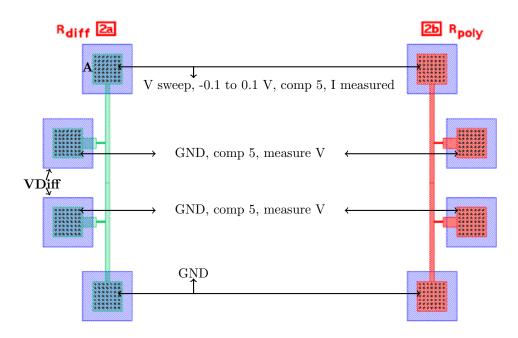


Figure 1: Device 2a is a diffusion resistor and 2b is a poly resistor.

## 1.2.2 I-V plot for the diffusion resistor, 2a

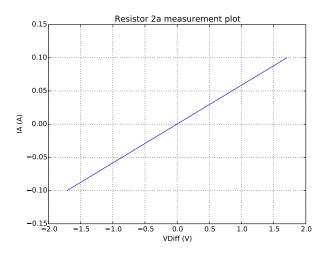


Figure 2: A plot of the measurement data taken for resistor 2a. The plot is based off of 2 data points.

Get resistance, sheet resistance, doping concentration, electron mobility ....

# 1.2.3 I-V plot for the poly resistor, 2b

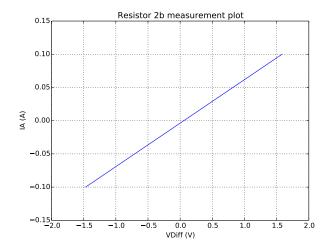


Figure 3: A plot of the measurement data taken for resistor 2b. The plot is based off of 2 data points.

Get resistance and sheet resistance...

# 1.3 Four-Point Contact-Chain Resistor [2c, 2d]

# 1.3.1 Measurement Setup

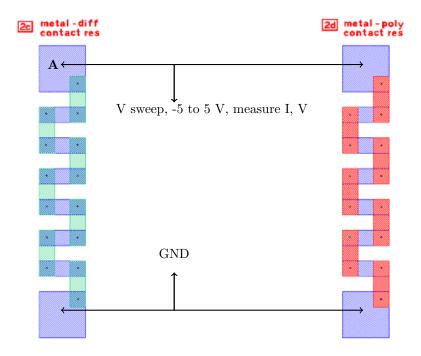


Figure 4: Chain resistor setup for diffusion and poly resistors.

## 1.3.2 b. I-V plot for diffusion resistor, 2c

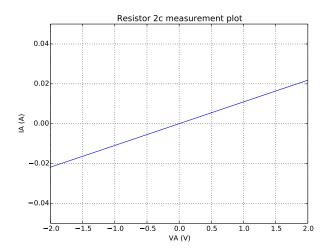


Figure 5: A plot of the measurement data taken for resistor 2c. The plot is based off of 2 data points.

- i. Extract the resistance
- ii. Extract metal-to-diffusion contact resistance

## 1.3.3 b. I-V plot for poly resistor, 2d

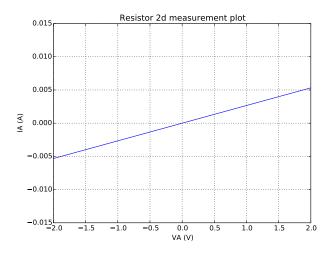


Figure 6: A plot of the measurement data taken for resistor 2d. The plot is based off of 2 data points.

- i. Extract the resistance
- ii. Extract metal-to-poly contact resistance

# 1.4 Gate Oxide Capacitor, 4

- 1.4.1 Measurement Setup
- 1.4.2 C-V plot of gate oxide capacitor w/ lights ON

Minimum capacitance

## 1.4.3 C-V plot of gate oxide capacitor w/ lights OFF

minimum capacitance ...

# 1.5 Field Oxide Capacitor, 3

## 1.5.1 Measurement Setup

## 1.5.2 C-V plot of field oxide capacitor

Minimum capacitance

## 1.5.3 Capacitance in the accumulation region

minimum capacitance ...

#### 1.5.4 Field oxide thickness

stuff...

# 1.6 Intermediate Oxide Capacitors, 5

- 1.6.1 Measurement Setup
- 1.6.2 C-V plot of intermediate oxide capacitor

stuff  $\dots$ 

#### 1.6.3 Capacitance in the accumulation region

stuff...

# 1.7 Diode, 7

# 1.7.1 Measurement setups for forward and reverse operations

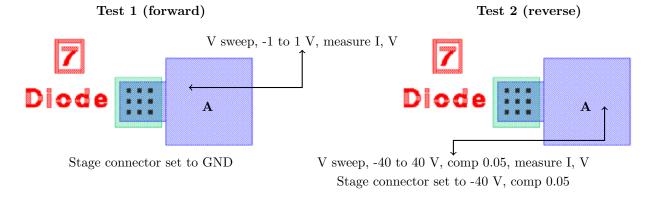
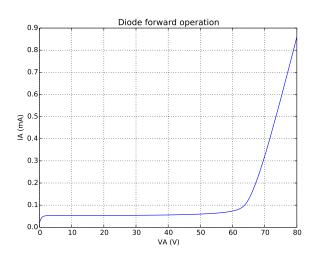


Figure 7: Two tests were performed on this diode; both measurement setups are shown above.

## 1.7.2 I-V plots for forward and reverse operation



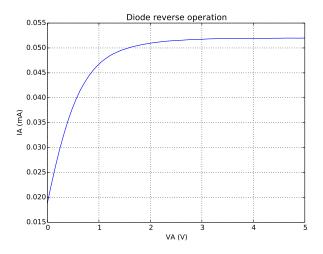


Figure 8: Plots of forward and reverse operation of Diode 7.

#### 1.7.3 Extract the turn-on voltage and the series resistance

# 1.8 MOSFETs of Varying Length, [8a-d]

## 1.8.1 Measurement setups

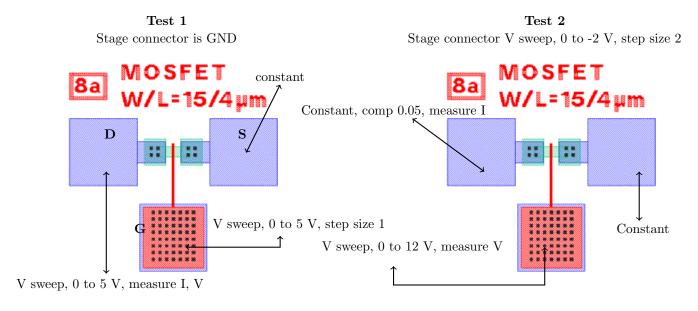


Figure 9: Measurement setup for Mosfet 8a. The same setup is used for Mosfets 8a-d. The only difference is the channel length which changes from 4 (8a) to 6 (8b) to 8 (8c) to 10 (8d) microns.

## 1.8.2 Plots of $I_D$ - $V_{DS}$ , sweeping $V_G$

Mosfet 8a

# 2 References

1. Jaeger, Richard. Introduction to microelectronic fabrication. New Jersey: Prentice Hall, 2002. Print.